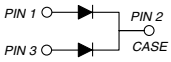
Dual Common-Cathode High-Voltage Schottky Rectifier

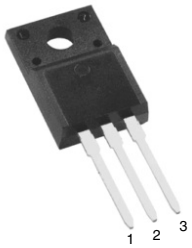
TO-262AA



SB10H150CT-1



ITO-220AB



MBRF10H150CT

FEATURES

- Guardring for overvoltage protection
- Low power loss, high efficiency
- Low forward voltage drop
- High frequency operation
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

RoHS COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency inverters, freewheeling and polarity protection applications.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-262AA

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102
E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

Mounting Torque: 10 in-lbs maximum

Polarity: As marked

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	2 x 5 A
V_{RRM}	150 V
I_{FSM}	160 A
V_F	0.72 V
T_J	175 °C

MAXIMUM RATINGS (T_C = 25 °C unless otherwise noted)

PARAMETER		SYMBOL	MBR10H150CT	UNIT
Maximum repetitive peak reverse voltage		V_{RRM}	150	V
Working peak reverse voltage		V_{RWM}	150	V
Maximum DC blocking voltage		V_{DC}	150	V
Maximum average forward rectified current (Fig. 1)	total device per diode	$I_{F(AV)}$	10 5	A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I_{FSM}	160	A
Peak repetitive reverse current per diode at t_p = 2 µs, 1 kHz		I_{RRM}	1.0	A
Peak non-repetitive reverse surge energy per diode (8/20 µs waveform)		E_{RSM}	10	mJ
Non-repetitive avalanche energy per diode at 25 °C, I_{AS} = 1.5 A, L = 10 mH		E_{AS}	11.25	mJ
Voltage rate of change (rated V_R)		dV/dt	10 000	V/µs
Operating junction and storage temperature range		T_J, T_{STG}	- 65 to + 175	°C
Isolation voltage (ITO-220AB only) from terminals to heatsink t = 1 min		V_{AC}	1500	V

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted)					
PARAMETER	**TEST CONDITIONS**		**SYMBOL**	**VALUE**	**UNIT**
Maximum instantaneous forward voltage per diode (1)	I_F = 5.0 A I_F = 5.0 A I_F = 10 A I_F = 10 A	T_J = 25 °C T_J = 125 °C T_J = 25 °C T_J = 125 °C	V_F	0.88 0.72 0.96 0.80	V
Maximum reverse current per diode at working peak reverse voltage (1)		T_J = 25 °C T_J = 125 °C	I_R	5.0 1.0	µA mA

Note:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted)					
PARAMETER	**SYMBOL**	**MBR**	**MBRF**	**MBRB**	**UNIT**
Typical thermal resistance per diode	$R_{\theta JC}$	2.4	4.5	2.4	°C/W

ORDERING INFORMATION (Example)					
PACKAGE	**PREFERRED P/N**	**UNIT WEIGHT (g)**	**PACKAGE CODE**	**BASE QUANTITY**	**DELIVERY MODE**
TO-220AB	MBR10H150CT-E3/45	2.06	45	50/tube	Tube
ITO-220AB	MBRF10H150CT-E3/45	2.20	45	50/tube	Tube
TO-262AA	SB10H150CT-1E3/45	1.58	45	50/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

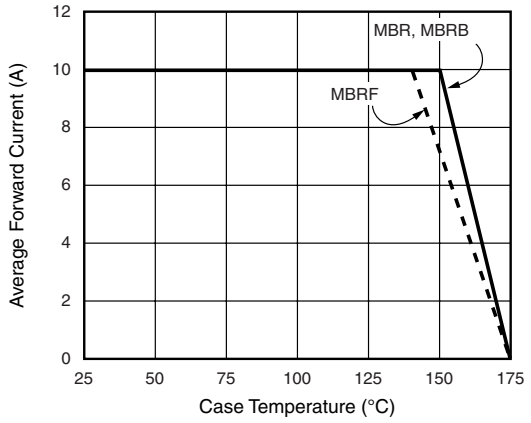


Figure 1. Forward Derating Curve (Total)

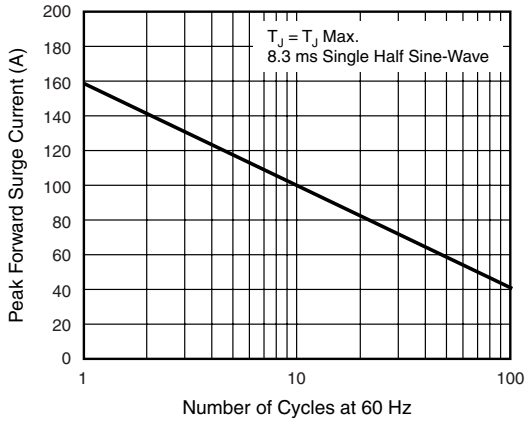


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

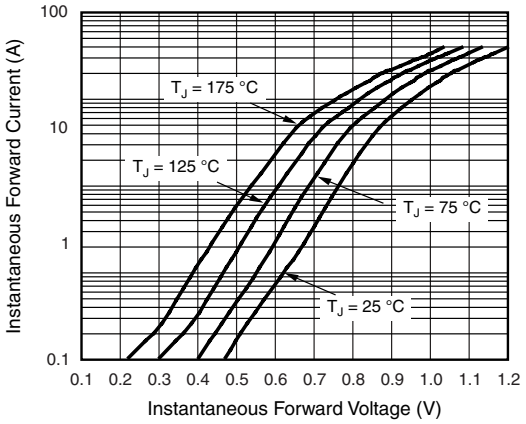


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

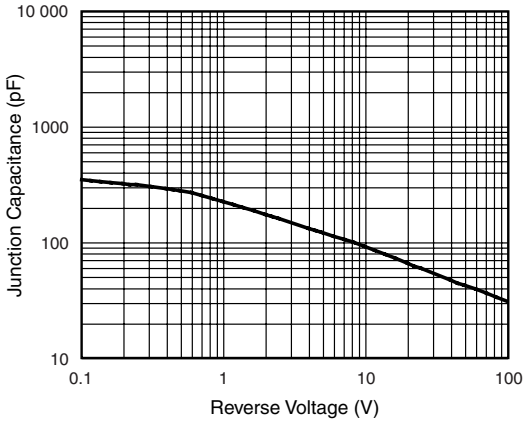


Figure 5. Typical Junction Capacitance Per Diode

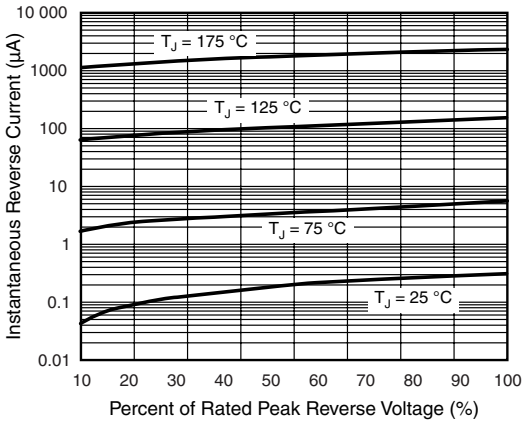


Figure 4. Typical Reverse Characteristics Per Diode

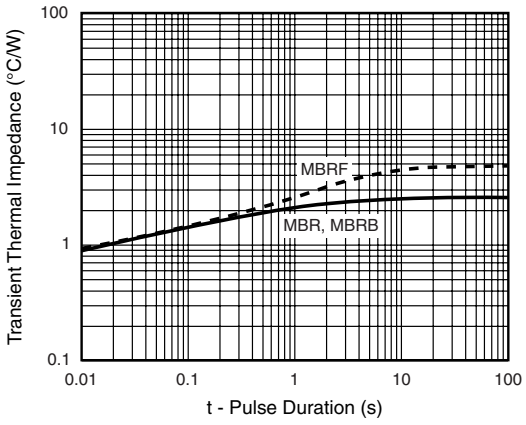
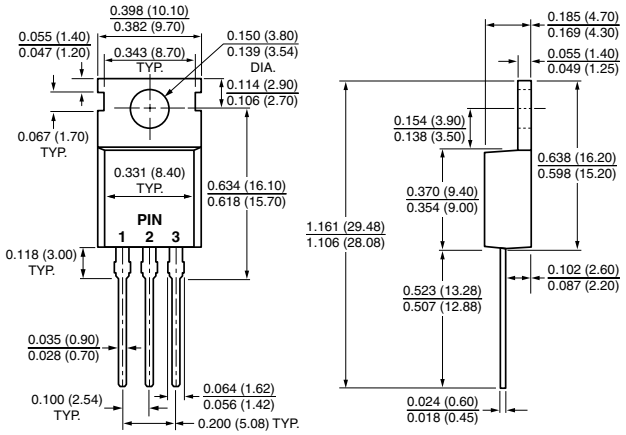


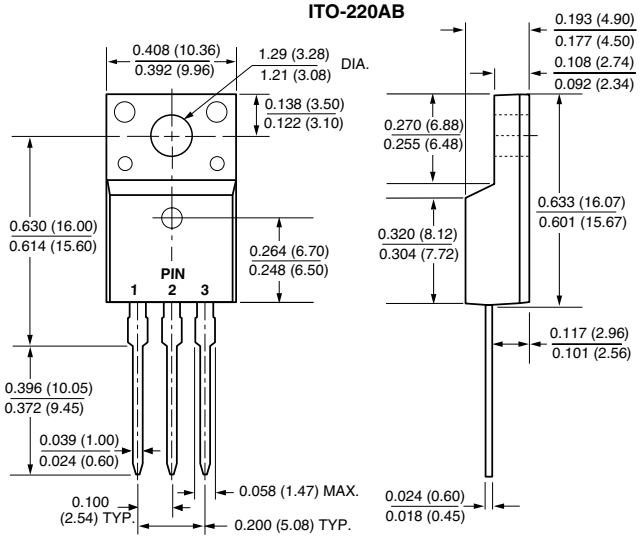
Figure 6. Typical Transient Thermal Impedance Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

TO-220AB



ITO-220AB



TO-262AA

